

## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$ Max	$I_D$ Max $T_A = +25^\circ C$
60V	$2\Omega @ V_{GS} = 10V$	380mA
	$3\Omega @ V_{GS} = 5V$	310mA

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Motor controls
- Power-management functions
- Backlighting

## Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.  
<https://www.diodes.com/quality/product-definitions/>
- An automotive-compliant part is available under separate datasheet ([2N7002KQ](#))

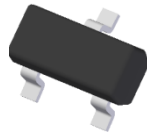
## Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

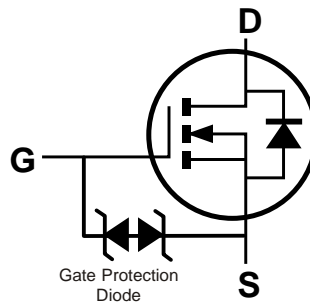


ESD protected up to 2kV

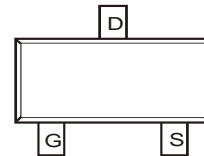
SOT23 (Standard)



Top View



Equivalent Circuit



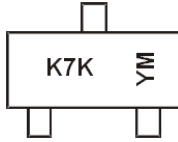
Top View

## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
2N7002K-7	SOT23 (Standard)	3,000	Tape & Reel
2N7002K-13	SOT23 (Standard)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



K7K = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  or  $\underline{Y}$  = Year (ex: L = 2024)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2006	-	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	T	-	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	380 300	mA
	t < 5s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	430 340	mA
Continuous Drain Current (Note 6) V <sub>GS</sub> = 5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	310 240	mA
	t < 5s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	350 270	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	0.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)			I <sub>DM</sub>	1.2	A

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P <sub>D</sub>	370	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	357	°C/W
	t < 5s		292	
Total Power Dissipation (Note 6)		P <sub>D</sub>	540	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	240	°C/W
	t < 5s		197	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	91	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

- Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.  
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	1.6	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.2	2.0	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5A
		—	1.4	3.0		V <sub>GS</sub> = 5V, I <sub>D</sub> = 0.05A
Forward Transfer Admittance	Y <sub>fs</sub>	80	—	—	ms	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Diode Forward Voltage	V <sub>SD</sub>	—	0.75	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	30	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	4.2	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.9	5.0	pF	f = 1MHz, V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V
Gate Resistance	R <sub>g</sub>	—	133	—	Ω	
Total Gate Charge	Q <sub>g</sub>	—	0.3	—	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.2	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.08	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.9	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 25Ω, I <sub>D</sub> = 200mA
Turn-On Rise Time	t <sub>r</sub>	—	3.4	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	15.7	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	9.9	—	ns	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

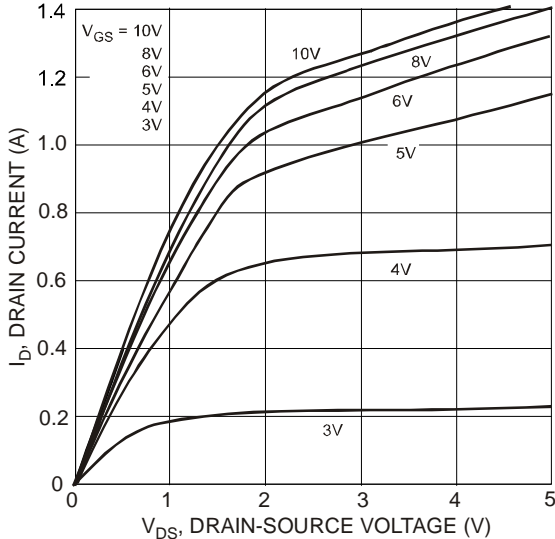


Fig. 1 Typical Output Characteristics

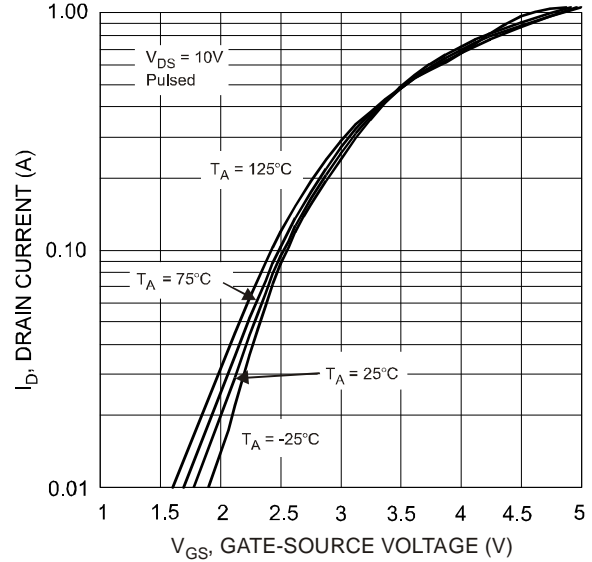


Fig. 2 Typical Transfer Characteristics

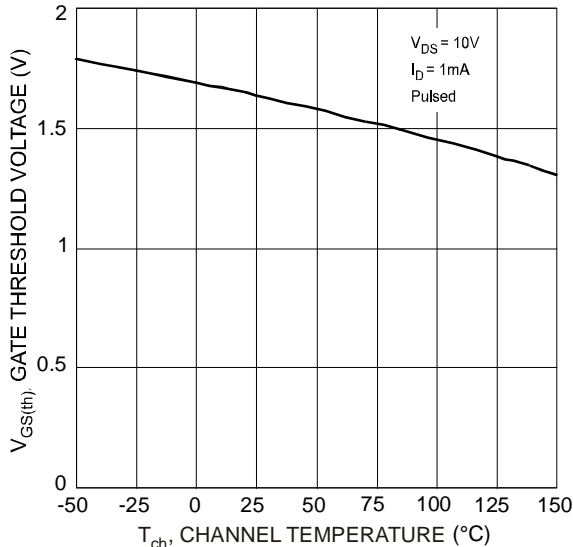


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

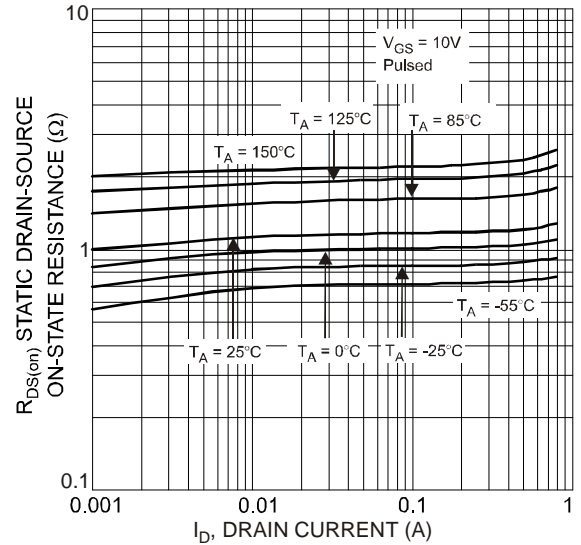


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

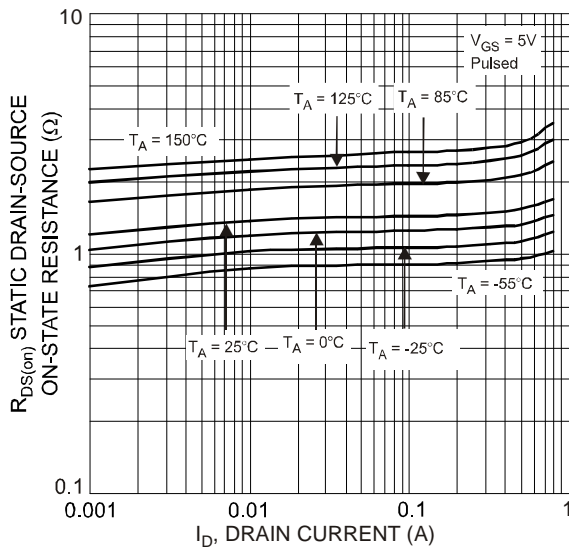


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

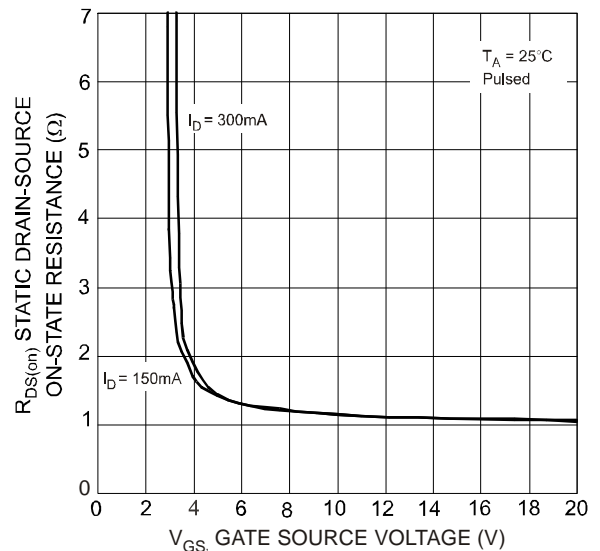


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

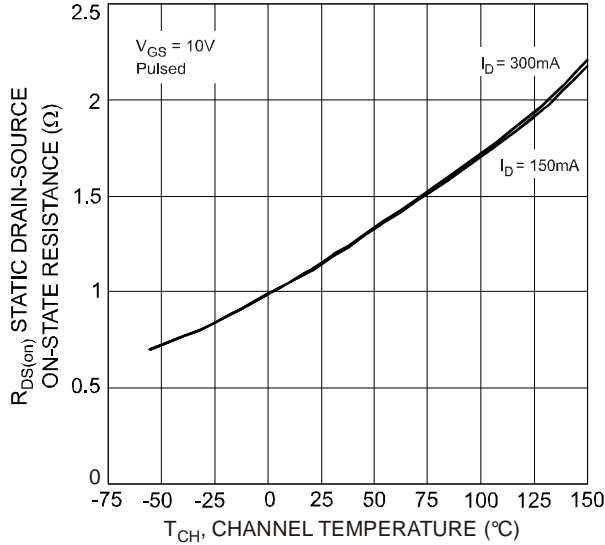


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

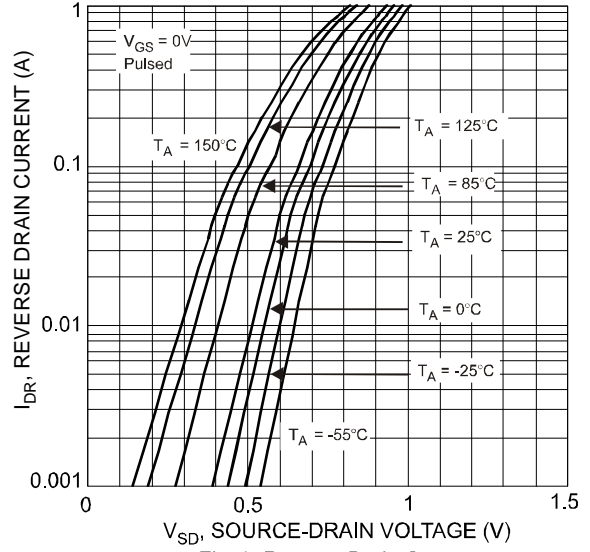


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

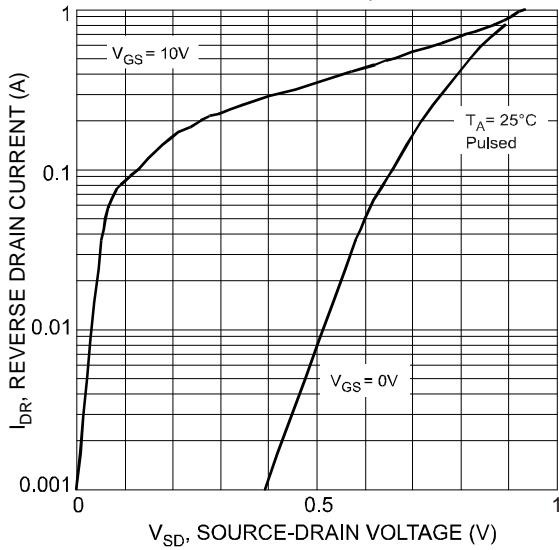


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

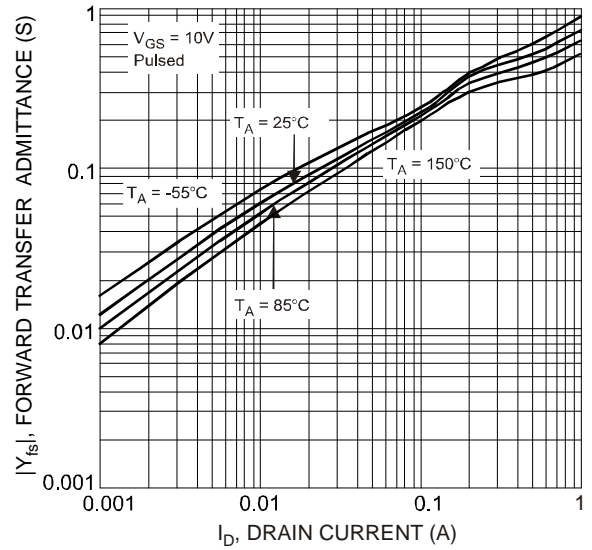


Fig. 10 Forward Transfer Admittance vs. Drain Current

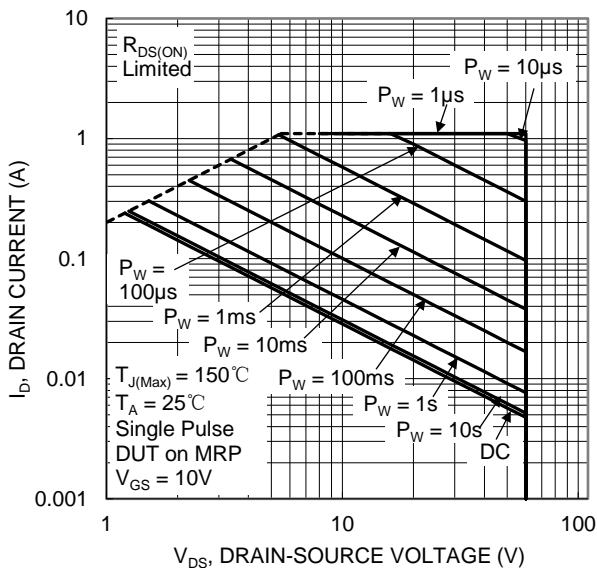


Fig. 11 SOA, Safe Operation Area

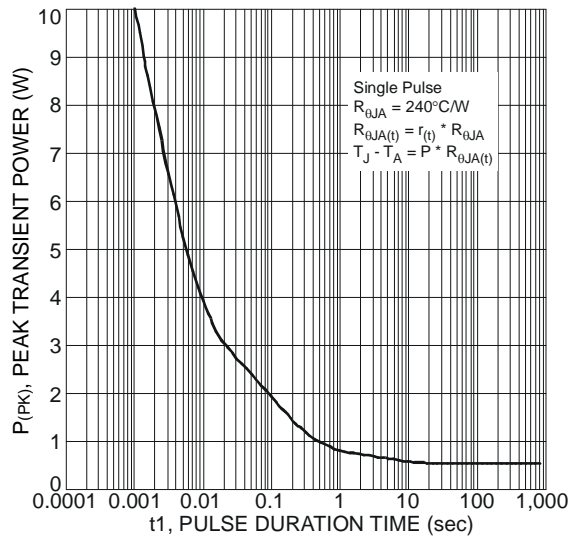


Fig. 12 Single Pulse Maximum Power Dissipation

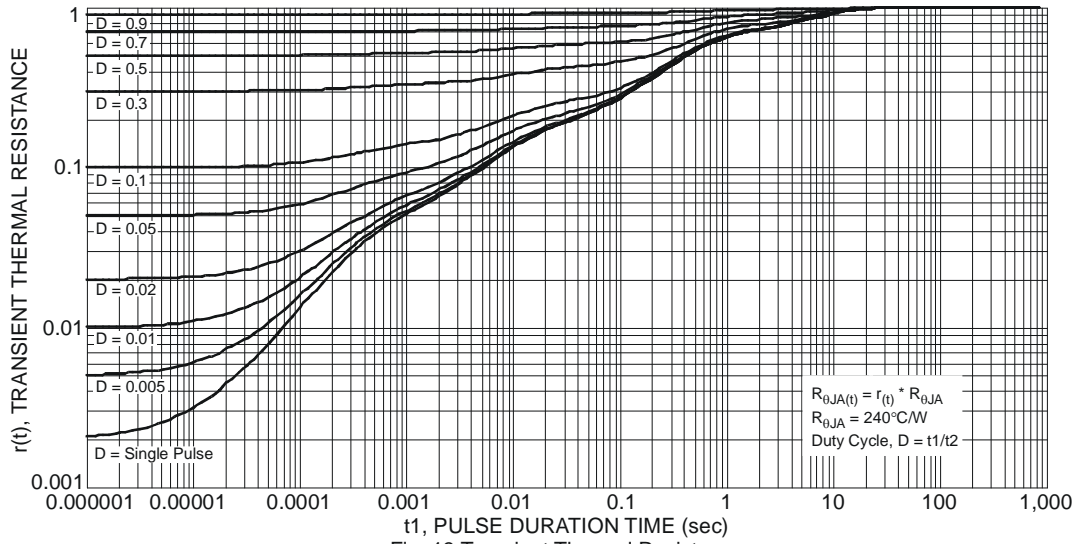
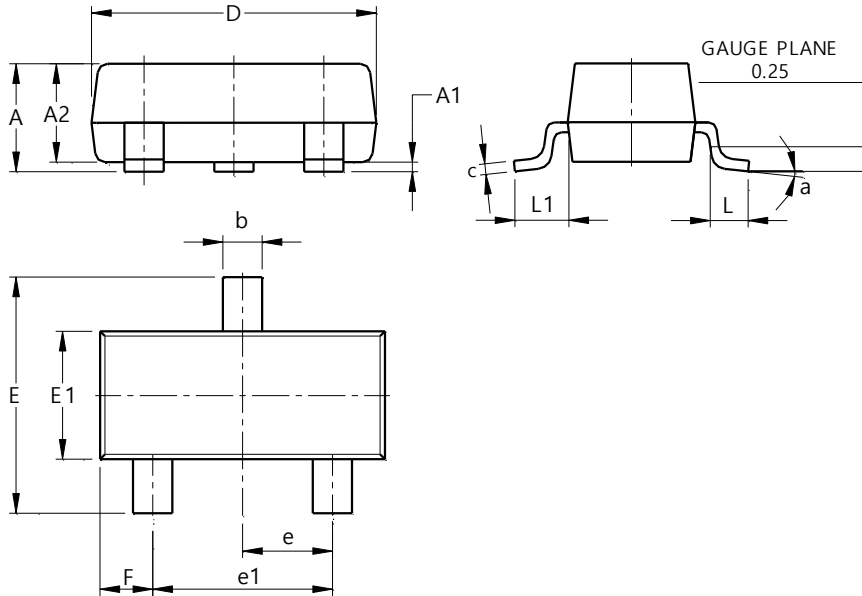


Fig. 13 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)

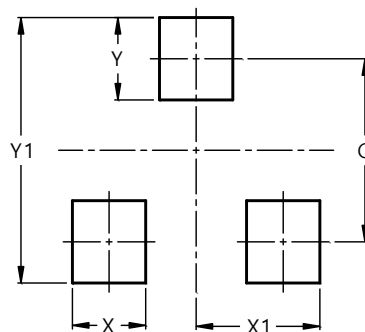


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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